

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = +25^\circ C$
-60V	150m Ω @ $V_{GS} = -10V$	-3A
	185m Ω @ $V_{GS} = -4.5V$	-2.7A

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) test in production
- Low on-resistance
- Fast switching speed
- **Lead-Free Finish; RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

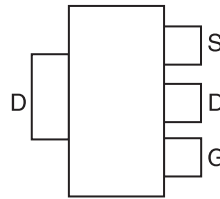
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.112 grams (approximate)

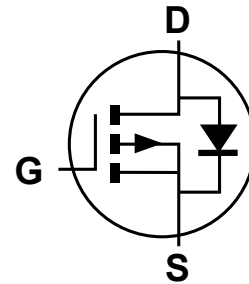
SOT223



Top View



Pin Out - Top View



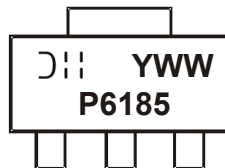
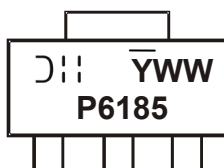
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMP6185SE-13	Standard	SOT223	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



$\text{D}|||$ = Manufacturer's Marking
 P6185 = Marking Code
 YWW = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 YWW = Date Code Marking for CAT (Chengdu Assembly/ Test site)
 Y or Y= Year (ex: 3 = 2013)
 WW = Week (01 - 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source voltage	V_{DSS}	-60	V
Gate-Source voltage	V_{GS}	± 20	V
Continuous Drain current (Note 6) $V_{GS} = -10\text{V}$	I_D	$T_A = +25^\circ\text{C}$	-3
		$T_A = +70^\circ\text{C}$	-2.4
Maximum Body Diode Continuous Current	I_S	-2	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)	I_{DM}	-15	A
Single Pulsed Avalanche Current (Note 7)	I_{AS}	-16	A
Single Pulsed Avalanche Energy (Note 7)	E_{AS}	13	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	$T_A = +25^\circ\text{C}$	1.2
		$T_A = +70^\circ\text{C}$	0.8
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	Steady state	104
		$t < 10\text{s}$	51
Total Power Dissipation (Note 6)	P_D	$T_A = +25^\circ\text{C}$	2.2
		$T_A = +70^\circ\text{C}$	1.4
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	Steady state	60
		$t < 10\text{s}$	30
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	7.6	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-60	-	-	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1	μA	$V_{DS} = -48\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	-1	-	-3	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	110	150	m Ω	$V_{GS} = -10\text{V}, I_D = -2.2\text{A}$
			130	185		$V_{GS} = -4.5\text{V}, I_D = -1.8\text{A}$
Diode Forward Voltage	V_{SD}	-	-0.75	-0.95	V	$V_{GS} = 0\text{V}, I_S = -1\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	708	-	pF	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{oss}	-	39	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	32	-	pF	
Gate Resistance	R_g	-	17	28	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = -4.5\text{V}$)	Q_g	-	6.2	-	nC	$V_{DS} = -30\text{V}, I_D = -12\text{A}$
Total Gate Charge ($V_{GS} = -10\text{V}$)	Q_g	-	14	-	nC	
Gate-Source Charge	Q_{gs}	-	2.8	-	nC	
Gate-Drain Charge	Q_{gd}	-	3.1	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	5.2	-	ns	
Turn-On Rise Time	t_r	-	23	-	ns	$V_{DS} = -30\text{V}, R_L = 2.5\Omega$ $V_{GS} = -10\text{V}, R_G = 3\Omega$
Turn-Off Delay Time	$t_{D(off)}$	-	33	-	ns	
Turn-Off Fall Time	t_f	-	39	-	ns	
Body Diode Reverse Recovery Time	t_{rr}	-	22	-	ns	$I_F = -12\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{rr}	-	17	-	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - UIS in production with $L = 0.1\text{mH}$, starting $T_A = +25^\circ\text{C}$.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

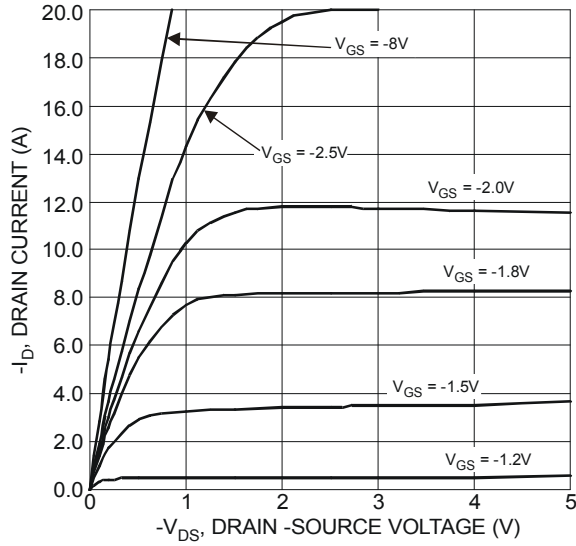


Figure 1 Typical Output Characteristics

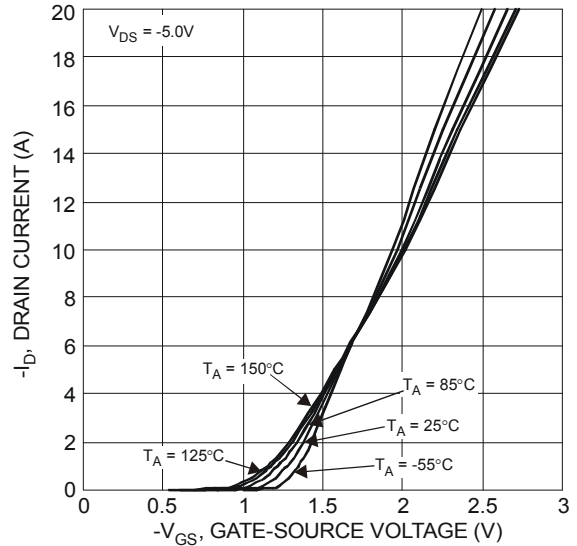


Figure 2 Typical Transfer Characteristics

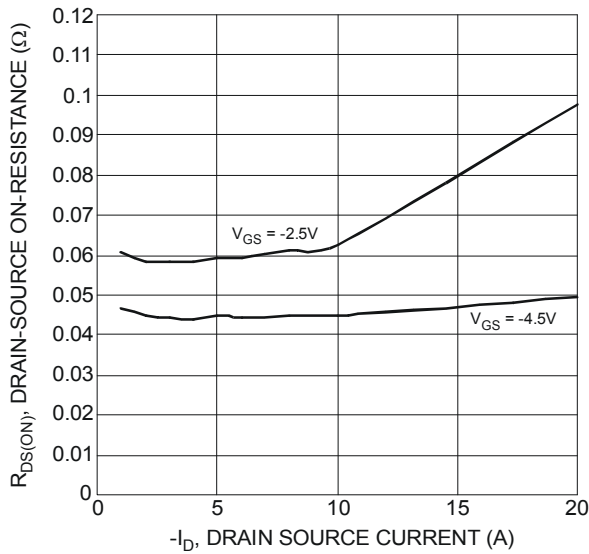


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

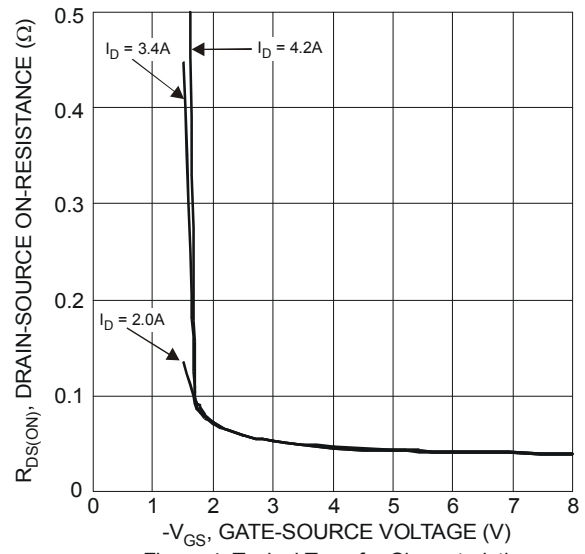


Figure 4 Typical Transfer Characteristics

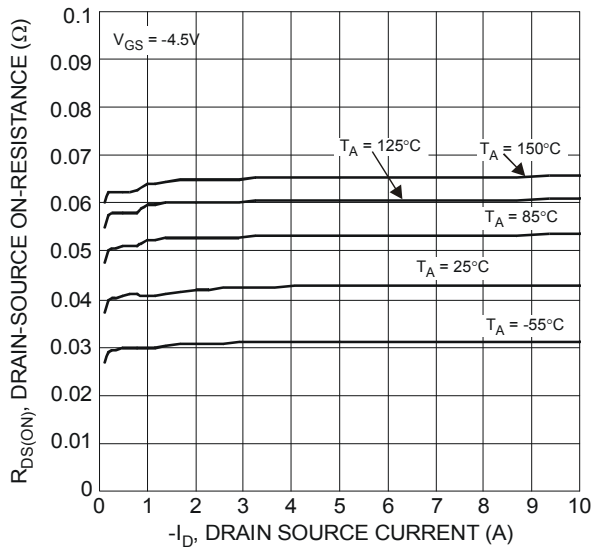


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

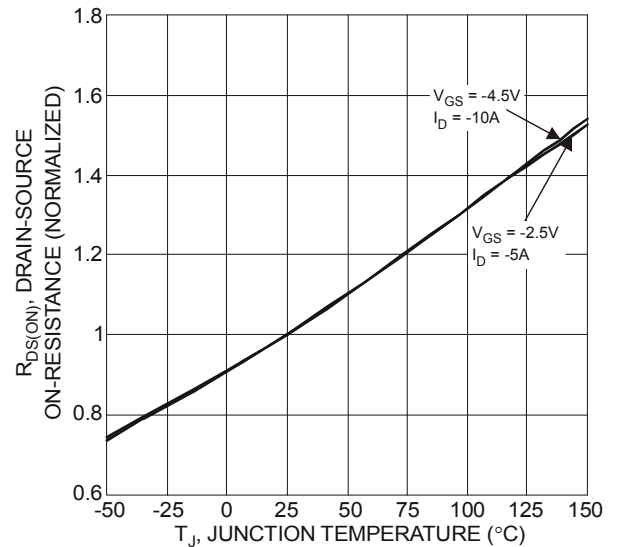
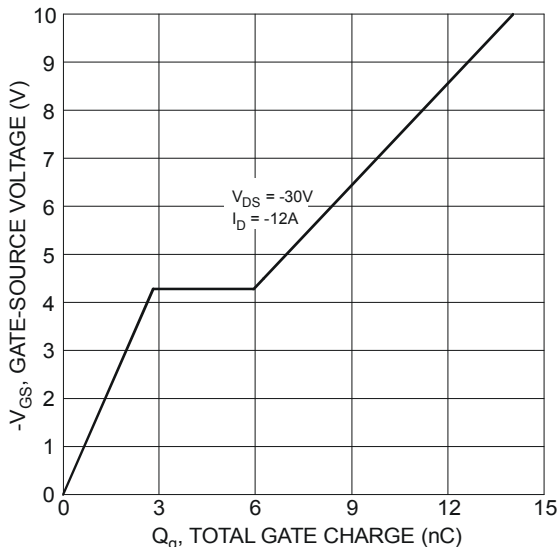
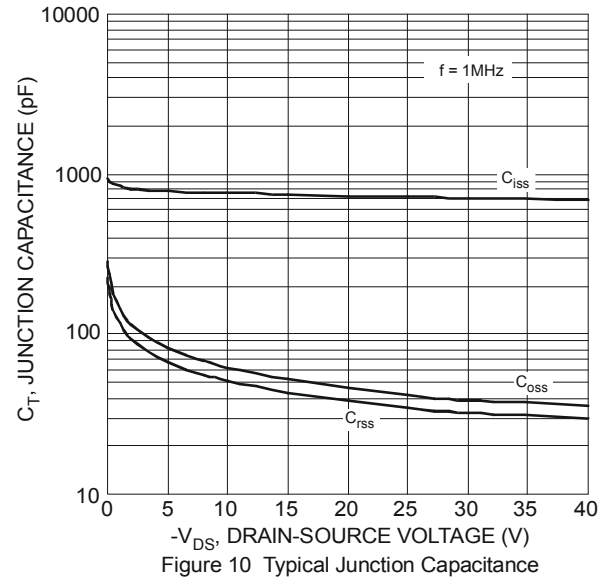
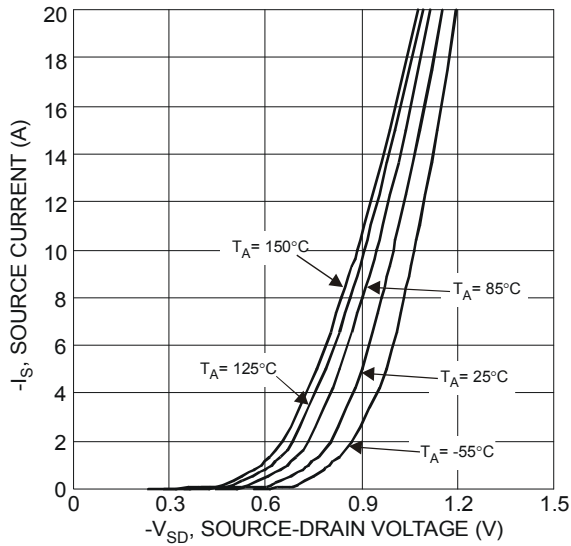
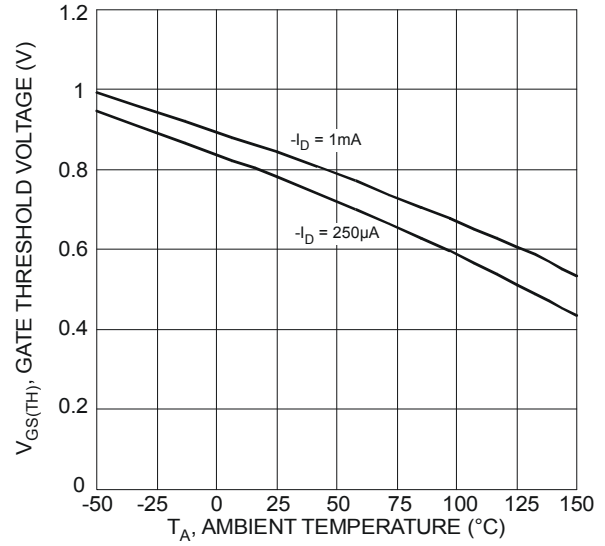
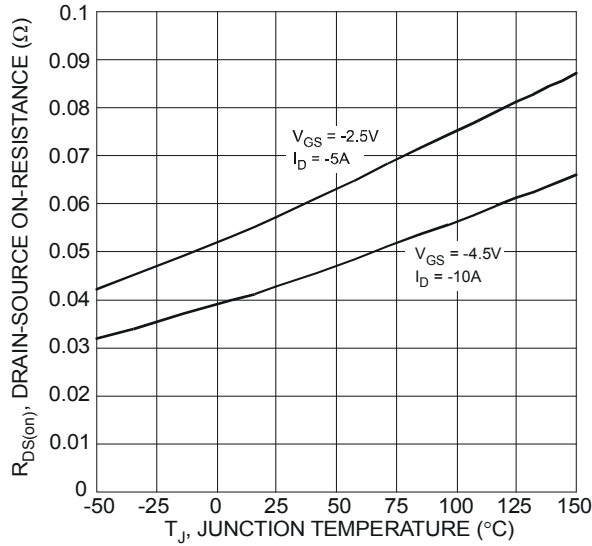
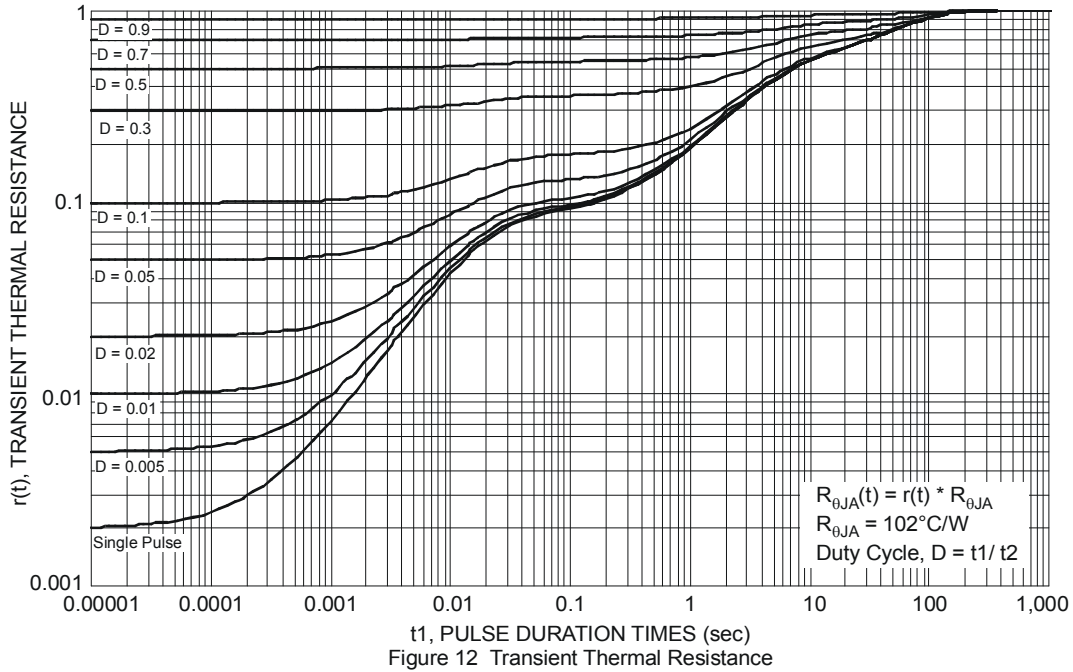


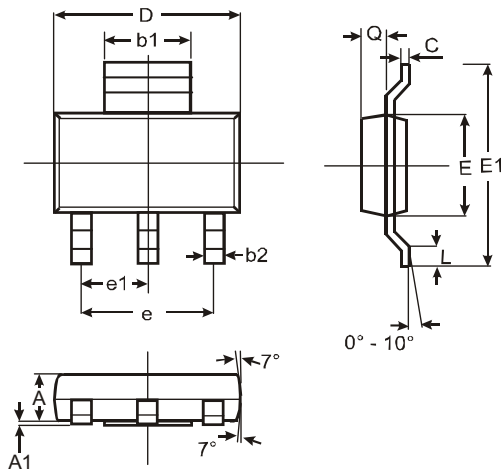
Figure 6 On-Resistance Variation with Temperature





Package Outline Dimensions

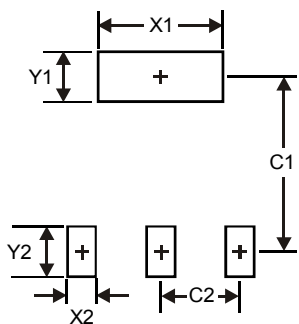
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b1	2.90	3.10	3.00
b2	0.60	0.80	0.70
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3

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